Spin-on-Glass P-210

<table>
<thead>
<tr>
<th>Elements of Interest</th>
<th>Key Element, atoms/cm³</th>
<th>Key Element % in Film</th>
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<tbody>
<tr>
<td>Si, O, P</td>
<td>P, 1x10²¹</td>
<td>Phosphorus</td>
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**Benefits**

- Light phosphorus doping level
- Uniform coatings
- Easy shipping without POCl₃ complications
- Uniform coatings
- Lower melting point than silica alone
- Lower maintenance and cost of ownership
- Stable processing independent of flow rates
- High purity materials
- Available with impurity specification of less than 1 ppm or less than 50 ppb.

**Typical Application**

This is a standard phosphorus doped silicate glass very typical for semiconductor applications. It begins curing at about 200°C to give a less dense but solid film. It continues to become increasingly dense as bake temperatures rise to 650°C or higher. We recommend baking at the highest temperature the material will see in any post processing if the material is to remain with the part. For doping applications the glass is often removed after the drive-in procedure.

The phosphorous in the glass matrix can act as a getter for sodium and other mobile ions. This reduces the effective concentration of unwanted ionic species.
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